



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	50mΩ @ V _{GS} = 10V	24A
	$65m\Omega$ @ V _{GS} = 4.5V	21A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Q_g Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMNH6042SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

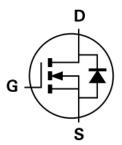
https://www.diodes.com/quality/product-definitions/

Mechanical Data

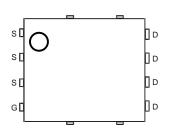
- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Bottom View



Internal Schematic



Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Pookogo	Packing			
Fait Number	Package	Qty.	Carrier		
DMNH6042SPSQ-13	PowerDI5060-8	2500	Tape & Reel		

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃!! = Manufacturer's Marking NH6042SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 24 = 2024) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit		
Drain-Source Voltage			VDSS	60	V		
Gate-Source Voltage			V _{GSS}	±20	V		
Continuous Drain Current (Note 7) Vgs = 10V	Steady State	T _C = +25°C T _C = +100°C	lD	24 17	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	35	Α		
Maximum Continuous Body Diode Forward Current (Note 8)			Maximum Continuous Body Diode Forward Current (Note 8)		Is	24	Α
Avalanche Current (Note 8) L = 10mH			las	3.5	Α		
Avalanche Energy (Note 8) L = 10mH			Eas	65	mJ		

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.5	W
Thermal Decistores Junction to Ambient (Note 5)	Steady state	7	98	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	54	
Total Power Dissipation (Note 6)		P _D	2.9	W
Thermal Decistores, Junction to Ambient (Note 6)	Steady state		51	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	26	
Thermal Resistance, Junction to Case (Note 7)	R _θ JC	3.5		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage		60	-	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	l		1	μΑ	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0		3.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		34	50	mΩ	V _G S = 10V, I _D = 5.1A	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	1	45	65	11122	$V_{GS} = 4.5V, I_{D} = 4.4A$	
Diode Forward Voltage	VsD	_	8.0	1.2	V	V _G S = 0V, I _S = 2.6A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	-	584	_	pF	05)/)/ 05)/	
Output Capacitance	Coss	1	83	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	1	24	_	pF	1 = 1.000112	
Gate Resistance	R_g		3.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	1	4.2	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g		8.8	_	nC	\/ 44\/ I- 5.0A	
Gate-Source Charge	Qgs	_	1.8	_	nC	$V_{DS} = 44V, I_{D} = 5.2A$	
Gate-Drain Charge	Qgd	_	1.8	_	nC	1	
Turn-On Delay Time	tD(ON)	_	3.4	_	ns		
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	tD(OFF)		10.1	_	ns	$R_G = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _F	_	4.5	_	ns	7	
Body Diode Reverse Recovery Time	t _{RR}		12.9	_	ns	$I_F = 2.6A$, $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge			5.4	_	nC	I _F = 2.6A, di/dt = 100A/µs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_{J} = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

DMNH6042SPSQ



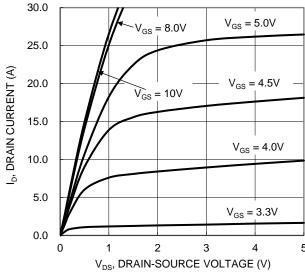


Figure 1. Typical Output Characteristic

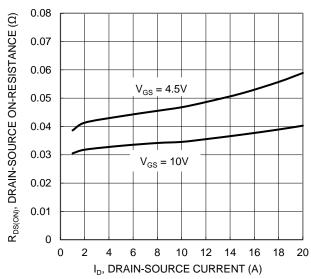


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

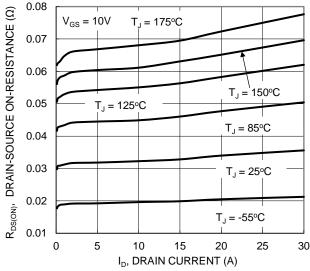


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

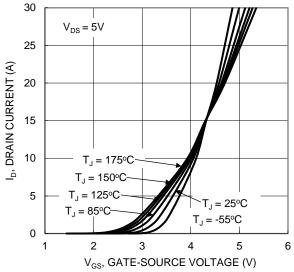


Figure 2. Typical Transfer Characteristic

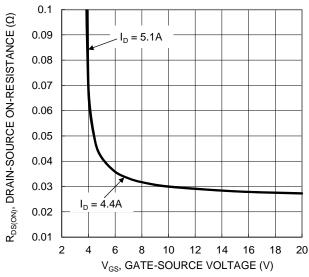


Figure 4. Typical Transfer Characteristic

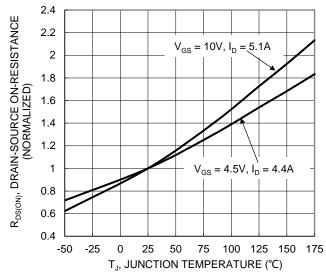


Figure 6. On-Resistance Variation with Temperature





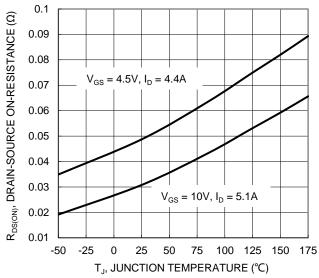
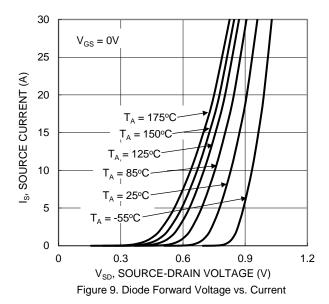


Figure 7. On-Resistance Variation with Temperature

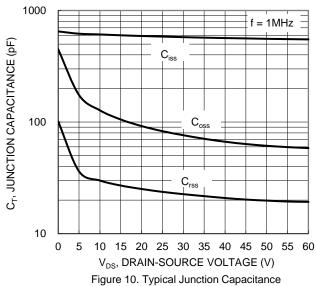


 $V_{DS} = 44V, I_{D} = 5.2A$ $V_{DS} = 44V, I_{D} = 6$ $V_{DS} = 44V, I_{D} = 6$ $V_{DS} = 44V, I_{D} = 5.2A$

Figure 11. Gate Charge

2.8 $V_{\text{GS(TH)}}$, GATE THRESHOLD VOLTAGE (V) 2.6 2.4 2.2 $I_D = 1mA$ 2 1.8 $I_{D} = 250 \mu A$ 1.6 1.4 1.2 75 100 125 150 -50 -25 0 25 50 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature



100 $R_{\text{DS}(\text{ON})}$ Limited 10 ID, DRAIN CURRENT (A) P_w=10ms P_W=100ms $T_{J(Max)} = 175$ °C 0.1 T_C=25°C Single Pulse DUT on infinite heatsink V_{GS}=10V 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area

10



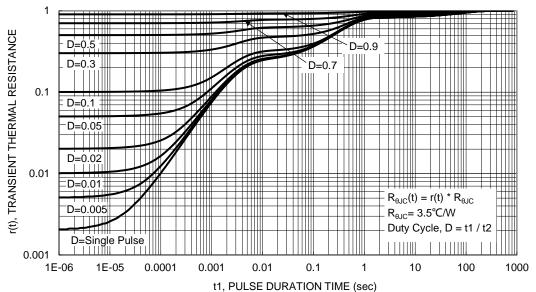


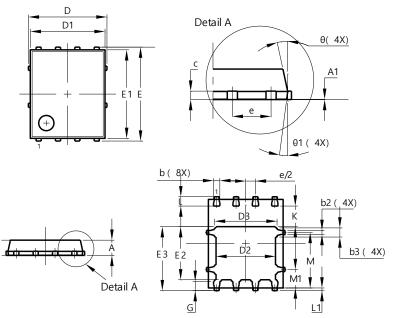
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

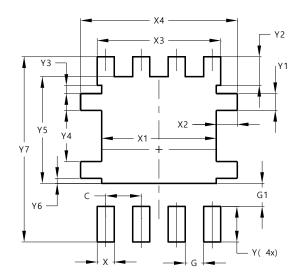


PowerDI5060-8				
Dim	Min	Тур		
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
C	0.230	0.330	0.277	
D	,	5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1.27 BSC			
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



IMPORTANT NOTICE

- 1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.
- 9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. All other trademarks are the property of their respective owners.

© 2024 Diodes Incorporated. All Rights Reserved.

www.diodes.com